



<b>Title of Change:</b>	Mold compound change due to End of Life of Samsung SDI molding compound in TO247.	
<b>Proposed first ship date:</b>	19 December 2019 or earlier upon customer approval.	
<b>Contact information:</b>	Contact your local ON Semiconductor Sales Office or <David.Zhu@onsemi.com>.	
<b>Samples:</b>	Contact your local ON Semiconductor Sales Office or <David.Zhu@onsemi.com>. Sample requests are to be submitted no later than 30 days from the date of first notification, IPCN or Final PCN, for this change. Samples delivery timing will be subject to request date, sample quantity and special customer packing/label requirements.	
<b>Additional Reliability Data:</b>	Contact your local ON Semiconductor Sales Office or <Lake.Wang@onsemi.com>.	
<b>Type of notification:</b>	This is a Final Product/Process Change Notification (FPCN) sent to customers. FPCNs are issued 90 days prior to implementation of the change. ON Semiconductor will consider this change accepted, unless an inquiry is made in writing within 30 days of delivery of this notice. To do so, contact <PCN.Support@onsemi.com>	
<b>Change Part Identification:</b>	Product with date code 1945 or newer will be assembled with a new mold compound.	
<b>Change Category:</b>	<input type="checkbox"/> Wafer Fab Change <input checked="" type="checkbox"/> Assembly Change <input type="checkbox"/> Test Change <input type="checkbox"/> Other _____	
<b>Change Sub-Category(s):</b>	<input type="checkbox"/> Manufacturing Site Addition <input checked="" type="checkbox"/> Material Change <input type="checkbox"/> Datasheet/Product Doc change <input type="checkbox"/> Manufacturing Site Transfer <input type="checkbox"/> Product specific change <input type="checkbox"/> Shipping/Packaging/Marking <input type="checkbox"/> Manufacturing Process Change <input type="checkbox"/> Other: _____	
<b>Sites Affected:</b>	ON Semiconductor Sites: ON Suzhou, China	External Foundry/Subcon Sites: None
<b>Description and Purpose:</b>		
ON Semiconductor wishes to inform our customers of a change in mold compounds used for the devices listed in this PCN. This change is a result of an End of Life notification received from Samsung for several of their SDI Mold Compounds. Due to the discontinuance of the SDI mold compounds, ON Semiconductor will only have limited supplies of the existing material and in some cases this may not allow for the normal change notification period. All other aspects of the impacted products (form, fit, function) will remain unchanged.		
	<b>Before Change Description</b>	<b>After Change Description</b>
Mold Compound (TO247-2 Package)	SG8200DL/SL7300HFM, Supplier: Samsung SDI	KTMC1050GFA
Mold Compound (TO247-3 Package)	SG8200DL/SL7300HFM, Supplier: Samsung SDI	KTMC1050GFA
Mold Compound (TO247-4 Package)	SG8200DL, Supplier: Samsung SDI	KTMC1050GFA
Mold Compound (TP247-3 Package)	SG8200DL/SL7300HFM, Supplier: Samsung SDI	KTMC1050GFA

**Reliability Data Summary:****QV DEVICE NAME:** RHRG75120**RMS** : U56686**PACKAGE** : TO247

Test	Specification	Condition	Interval	Results
HTRB	JESD22-A108	Ta = 175°C for device, bias = 80% of max rated	1008 hrs	0/77
HTSL	JESD22-A103	Ta = 175°C for 1008 hours	1008 hrs	0/77
TC	JESD22-A104	Temp = -55°C to +150°C; for 1000 cycles	1000 cyc	0/77
H3TRB	JESD22-A101	Temp = 85C, RH=85%, bias = 80% of rated V or 100V max	1008 hrs	0/77
RSH	JESD22-B106	265 °C Immersion and 10s	10s	0/10
SD	J STD 002	Ta=245°C 5 sec dwell	5s	0/15
PD		Per Case Outline		0/10
Tri-temp		Tri-Temp Characterization, Per 48A		0/30
TR		Thermal Resistance		0/10

**QV DEVICE NAME:** FGY75T120SQDN**RMS** : U56694**PACKAGE** : TO247

Test	Specification	Condition	Interval	Results
HTRB	JESD22-A108	Ta = 175°C for device, bias = 80% of max rated	1008 hrs	0/77
HTGB	JESD22-A108	Ta = 175°C for 1008 hours, 100% rated Vgs	1008 hrs	0/77
HTSL	JESD22-A103	Ta = 175°C for 1008 hours	1008 hrs	0/77
TC	JESD22-A104	Temp = -55°C to +150°C; for 1000 cycles	1000 cyc	0/77
HAST	JESD22 A110	Temp= +110°C, RH=85% , 264hr, bias = 80% of rated V or 100V max	264hrs	0/77
RSH	JESD22-B106	265 °C Immersion and 10s	10s	0/10
SD	J STD 002	Ta=245°C 5 sec dwell	5s	0/15
PD		Per Case Outline		0/10
Tri-temp		Tri-Temp Characterization, Per 48A		0/30
TR		Thermal Resistance		0/10

**QV DEVICE NAME:** FGY160T65SPD-F085**RMS** : U56679**PACKAGE** : TO247

Test	Specification	Condition	Interval	Results
HTRB	JESD22-A108	Ta = 175°C for device, bias = 100% of max rated	1008 hrs	0/231
HTGB	JESD22-A108	Ta = 175°C for 1008 hours, 100% rated Vgs	1008 hrs	0/231
HTSL	JESD22-A103	Ta = 175°C for 1008 hours	1008 hrs	0/231
TC	JESD22-A104	Temp = -55°C to +150°C; for 1000 cycles	1000 cyc	0/231
IOL	MIL STD750, M 1037 AEC Q101	Ta=+25°C, delta Tj=100°C max, Ton=Toff is 3.5min	8572Cyc	0/231
H3TRB	JESD22-A101	Temp = 85°C, RH=85%, bias = 80% of rated V or 100V max	1008hrs	0/231
RSH	JESD22-B106	265 °C Immersion and 10s	10s	0/30
SD	J STD 002	Ta=245°C 5 sec dwell	5s	0/45
PD		Per Case Outline		0/30
Tri-temp		Tri-Temp Characterization, Per 48A		0/90
TR		Thermal Resistance		0/30
CDPA TCDT	AEC Q101, rev D, test 7A (alt)	Custom Destructive Physical Analysis - TC Delamination Test, Post 1000 cyc TC		0/66
CDPA SAT	AEC-006	Post HTRB,HTGB		0/66



DPA	AEC-Q101-004 Section 4	Destructive Physical Analysis Post TC, H3TRB, HTRB, HTGB	0/6
CDPA WP BS	MIL 883E, AEC - 006	Custom Destructive Physical Analysis - Wire Pull, Ball Shear Post TC, HTRB, HTGB	0/18
CDPA X Section	AEC -006	Post TC, HTRB, HTGB	0/9
Shift		Shift Analysis for HTRB/HTGB/HTSL/TC/IOL/H3TRB	Pass

**QV DEVICE NAME:** FFSH40120ADN-F085

**RMS** : U56690

**PACKAGE** : TQ247

Test	Specification	Condition	Interval	Results
HTRB	JESD22-A108	Ta = 175°C for device, bias = 100% of max rated	1008 hrs	0/231
HTSL	JESD22-A103	Ta = 175°C for 1008 hours	1008 hrs	0/231
TC	JESD22-A104	Temp = -55°C to +150°C; for 1000 cycles	1000 cyc	0/231
HAST	JESD22 A110	Temp= +110°C, RH=85% , 264hr, bias = 80% of rated V or 100V max	264hrs	0/231
RSH	JESD22-B106	265 °C Immersion and 10s	10s	0/30
SD	J STD 002	Ta=245°C 5 sec dwell	5s	0/45
PD		Per Case Outline		0/30
Tri-temp		Tri-Temp Characterization, Per 48A		0/90
TR		Thermal Resistance		0/30
CDPA TCDT	AEC Q101, rev D, test 7A (alt)	Custom Destructive Physical Analysis - TC Delamination Test, Post 1000 cyc TC		0/66
CDPA SAT	AEC-006	Post HTRB		0/66
DPA	AEC-Q101-004 Section 4	Destructive Physical Analysis Post TC, HAST, HTRB		0/6
CDPA WP BS	MIL 883E, AEC - 006	Custom Destructive Physical Analysis - Wire Pull, Ball Shear Post TC, HTRB		0/18
CDPA X Section	AEC -006	Post TC, HTRB		0/9
Shift		Shift Analysis for HTRB/HTGB/HTSL/TC/IOL/HAST		Pass

**QV DEVICE NAME:** SVHL080N120SC1

**RMS** : U56692

**PACKAGE** : TQ247

Test	Specification	Condition	Interval	Results
HTRB	JESD22-A108	Ta = 175°C for device, bias = 100% of max rated	1008 hrs	0/231
HTGB	JESD22-A108	Ta = 175°C for 1008 hours, 100% rated Vgs	1008 hrs	0/231
HTSL	JESD22-A103	Ta = 175°C for 1008 hours	1008 hrs	0/231
TC	JESD22-A104	Temp = -55°C to +150°C; for 1000 cycles	1000 cyc	0/231
IOL	MIL STD750, M 1037 AEC Q101	Ta=+25°C, delta Tj=100°C max, Ton=Toff is 3.5min	8572Cyc	0/231
HAST	JESD22 A110	Temp= +110°C, RH=85% , 264hr, bias = 80% of rated V or 100V max	264hrs	0/231
RSH	JESD22-B106	265 °C Immersion and 10s	10s	0/30
SD	J STD 002	Ta=245°C 5 sec dwell	5s	0/45
PD		Per Case Outline		0/30
Tri-temp		Tri-Temp Characterization, Per 48A		0/90
TR		Thermal Resistance		0/30
CDPA TCDT	AEC Q101, rev D, test 7A (alt)	Custom Destructive Physical Analysis - TC Delamination Test, Post 1000 cyc TC		0/66
CDPA SAT	AEC-006	Post HTRB,HTGB		0/66
DPA	AEC-Q101-004 Section 4	Destructive Physical Analysis Post TC, HAST, HTRB, HTGB		0/6



CDPA WP BS	MIL 883E, AEC - 006	Custom Destructive Physical Analysis - Wire Pull, Ball Shear Post TC, HTRB, HTGB		0/18
CDPA X Section	AEC -006	Post TC, HTRB, HTGB		0/9
Shift		Shift Analysis for HTRB/HTGB/HTSL/TC/IOL/HAST		Pass

**QV DEVICE NAME:** FCH041N60F-F085

**RMS** : U56699

**PACKAGE** : TO247

Test	Specification	Condition	Interval	Results
HTRB	JESD22-A108	Ta = 150°C for device, bias = 100% of max rated	1008 hrs	0/231
HTGB	JESD22-A108	Ta = 150°C for 1008 hours, 100% rated Vgs	1008 hrs	0/231
HTSL	JESD22-A103	Ta = 150°C for 1008 hours	1008 hrs	0/231
TC	JESD22-A104	Temp = -55°C to +150°C; for 1000 cycles	1000 cyc	0/231
IOL	MIL STD750, M 1037 AEC Q101	Ta=+25°C, delta Tj=100°C max, Ton=Toff is 3.5min	8572Cyc	0/231
HAST	JESD22 A110	Temp= +110°C, RH=85% , 264hr, bias = 80% of rated V or 100V max	264hrs	0/231
RSH	JESD22-B106	265 °C Immersion and 10s	10s	0/30
SD	J STD 002	Ta=245°C 5 sec dwell	5s	0/45
PD		Per Case Outline		0/30
Tri-temp		Tri-Temp Characterization, Per 48A		0/90
TR		Thermal Resistance		0/30
CDPA TCDT	AEC Q101, rev D, test 7A (alt)	Custom Destructive Physical Analysis - TC Delamination Test, Post 1000 cyc TC		0/66
CDPA SAT	AEC-006	Post HTRB,HTGB		0/66
DPA	AEC-Q101-004 Section 4	Destructive Physical Analysis Post TC, HAST, HTRB, HTGB		0/6
CDPA WP BS	MIL 883E, AEC - 006	Custom Destructive Physical Analysis - Wire Pull, Ball Shear Post TC, HTRB, HTGB		0/18
CDPA X Section	AEC -006	Post TC, HTRB, HTGB		0/9
Shift		Shift Analysis for HTRB/HTGB/HTSL/TC/IOL/HAST		Pass

All reliability result passed

**Electrical Characteristic Summary:**

Electrical characteristics are not impacted

**List of Affected Parts:**

**Note:** Only the standard (off the shelf) part numbers are listed in the parts list. Any custom parts affected by this PCN are shown in the customer specific PCN addendum in the PCN email notification, or on the **PCN Customized Portal**.

Part Number	Qualification Vehicle
FFH30S60STU	RHRG75120
FFH60UP40S3	RHRG75120
FFH60UP60S	RHRG75120
FFH60UP60S3	RHRG75120
ISL9K3060G3	RHRG75120



ISL9R1560G2	RHRG75120
ISL9R3060G2	RHRG75120
RHRG30120	RHRG75120
RHRG5060	RHRG75120
RHRG75120	RHRG75120
RURG3060	RHRG75120
RURG5060	RHRG75120
RURG8060	RHRG75120
FGH30S130P	FGY160T65SPD-F085
FGH30S150P	FGY160T65SPD-F085
FGH40N60UFTU	FGY160T65SPD-F085
FGH40T120SMDL4	FGY160T65SPD-F085
FGH50N6S2D	FGY160T65SPD-F085
FGH50T65SQD-F155	FGY160T65SPD-F085
FGH60N60SFDTU	FGY160T65SPD-F085
FGH60N60SFTU	FGY160T65SPD-F085
FGH60N60SMD	FGY160T65SPD-F085
FGH60N60UFDTU	FGY160T65SPD-F085
FGH60T65SQD-F155	FGY160T65SPD-F085
FGH75N60UFTU	FGY160T65SPD-F085
FGH75T65SQD-F155	FGY160T65SPD-F085
FGH75T65SQDNL4	FGY160T65SPD-F085
FGH75T65SQDT-F155	FGY160T65SPD-F085
FGH75T65SQDTL4	FGY160T65SPD-F085
FGH75T65UPD-F155	FGY160T65SPD-F085
FGH80N60FDTU	FGY160T65SPD-F085
FGY40T120SMD	FGY160T65SPD-F085
FGY75N60SMD	FGY160T65SPD-F085
HGTG30N60B3D	FGY160T65SPD-F085
HGTG7N60A4D	FGY160T65SPD-F085
FGHL50T65SQ	FGY160T65SPD-F085
FGHL40S65UQ	FGY160T65SPD-F085
FGY75T120SQDN	FGY75T120SQDN
FGH40T120SQDNL4	FGY75T120SQDN



FGY60T120SQDN	FGY75T120SQDN
FFSH10120A	FFSH40120ADN-F085
FFSH10120ADN-F155	FFSH40120ADN-F085
FFSH15120A	FFSH40120ADN-F085
FFSH15120ADN-F155	FFSH40120ADN-F085
FFSH1665A	FFSH40120ADN-F085
FFSH1665ADN-F155	FFSH40120ADN-F085
FFSH20120A	FFSH40120ADN-F085
FFSH20120ADN-F155	FFSH40120ADN-F085
FFSH2065A	FFSH40120ADN-F085
FFSH2065ADN-F155	FFSH40120ADN-F085
FFSH30120A	FFSH40120ADN-F085
FFSH30120ADN-F155	FFSH40120ADN-F085
FFSH3065A	FFSH40120ADN-F085
FFSH3065ADN-F155	FFSH40120ADN-F085
FFSH40120A	FFSH40120ADN-F085
FFSH40120ADN-F155	FFSH40120ADN-F085
FFSH4065A	FFSH40120ADN-F085
FFSH4065ADN-F155	FFSH40120ADN-F085
FFSH50120A	FFSH40120ADN-F085
FFSH5065A	FFSH40120ADN-F085
FFSH5065A-F155	FFSH40120ADN-F085
NTHL080N120SC1	SVHL080N120SC1
NTH4L080N120SC1	SVHL080N120SC1
FCH041N65EF-F155	FCH041N60F-F085
FCH041N65EFL4	FCH041N60F-F085
FCH041N65F-F155	FCH041N60F-F085
FCH043N60	FCH041N60F-F085
FCH060N80-F155	FCH041N60F-F085
FCH070N60E	FCH041N60F-F085
FCH072N60F	FCH041N60F-F085
FCH077N65F-F155	FCH041N60F-F085
FCH085N80-F155	FCH041N60F-F085
FCH099N60E	FCH041N60F-F085



FCH104N60	FCH041N60F-F085
FCH104N60F	FCH041N60F-F085
FCH110N65F-F155	FCH041N60F-F085
FCH125N60E	FCH041N60F-F085
FCH150N65F-F155	FCH041N60F-F085
FCH165N60E	FCH041N60F-F085
FCH190N65F-F155	FCH041N60F-F085
FDH038AN08A1	FCH041N60F-F085
FDH055N15A	FCH041N60F-F085
FDH210N08	FCH041N60F-F085
FDH44N50	FCH041N60F-F085
FQH8N100C	FCH041N60F-F085
HUF75345G3	FCH041N60F-F085
HUF75652G3	FCH041N60F-F085
HUF75852G3	FCH041N60F-F085
FCH041N65EFLN4	FCH041N60F-F085

Japanese translation of the notification starts here.  
通知の日本語訳はここから始まります。

*Note: The Japanese version is for reference only. In case of any differences between the English and Japanese version, the English version shall control.*

注：日本語版は参照用です。英語版と日本語版の違いがある場合は、英語版が優先されます。





## 最終製品 / プロセス変更通知

文書番号# : FPCN22647XC

発行日 : 12 September 2019

変更件名:	TO247 における Samsung SDI 製モールドコンパウンドの生産終了に伴うモールドコンパウンドの変更	
初回出荷予定日:	19 December 2019 またはお客様からの承認が得られた場合はそれ以前.	
連絡先情報:	現地のオン・セミコンダクター営業所または <David.Zhu@onsemi.com> にお問い合わせください。	
サンプル:	現地のオン・セミコンダクター営業所または <David.Zhu@onsemi.com> にお問い合わせください。 サンプルは、この変更の初回通知、初回 PCN の日付から 30 日以内に要求してください。 サンプル納入時は、依頼日、数量、特別梱包材/ラベル条件によって異なります。	
追加の信頼性データ:	お客さまの地域のオン・セミコンダクター営業所または <Lake.Wang@onsemi.com> にお問い合わせください。	
通知種別: :	これは、お客様宛の最終製品 / プロセス変更通知 (FPCN) です。FPCN は、変更実施の 90 日前に発行され ます。 オン・セミコンダクターは、この通知の送付から 30 日以内に書面による問い合わせがない限り、この変更が承諾され たものとみなします。お問い合わせは、<PCN.Support@onsemi.com> 宛てにお願いします。	
変更部品の識別:	日付コード 1945 以降の製品は、新しいモールドコンパウンドで組み立てられます。	
変更カテゴリ:	<input type="checkbox"/> ウェハファブの変更 <input checked="" type="checkbox"/> アセンブリの変更 <input type="checkbox"/> 試験の変更 <input type="checkbox"/> その他 _____	
変更サブカテゴリ:	<input type="checkbox"/> 製造拠点の追加 <input checked="" type="checkbox"/> 材料の変更 <input type="checkbox"/> データシート/製品資料の変更 <input type="checkbox"/> 製造拠点の移転 <input type="checkbox"/> 製品仕様の変更 <input type="checkbox"/> 出荷/パッケージング/表記 <input type="checkbox"/> 製造プロセスの変更 <input type="checkbox"/> その他: _____	
影響を受ける拠点:	オン・セミコンダクター拠点: ON Suzhou, China	外部製造工場 / 下請業者拠点: なし
<b>説明および目的:</b> <p>オン・セミコンダクターは、本 FPCN に列記された製品に対するモールドコンパウンドの変更をお客様にお知らせいたします。この変更は、SDI モールドコンパウンドのいくつかについてサムソンから受けた生産終了の通知によるものです。SDI モールドコンパウンドの廃止によって、オン・セミコンダクターでは既存の材料の供給が限定されるようになるため、場合によっては、このことによって通常の変更通知期間が不可能になる場合があります。対象となる製品の他の特徴(形状、適合性、機能)には変更はありません。</p>		
	<b>変更前の表記</b>	<b>変更後の表記</b>
モールド・コンパウンド (TO247-2 Package)	SG8200DL/SL7300HFM, Supplier: Samsung SDI	KTMC1050GFA
モールド・コンパウンド (TO247-3 Package)	SG8200DL/SL7300HFM, Supplier: Samsung SDI	KTMC1050GFA
モールド・コンパウンド (TO247-4 Package)	SG8200DL, Supplier: Samsung SDI	KTMC1050GFA
モールド・コンパウンド (TP247-3 Package)	SG8200DL/SL7300HFM, Supplier: Samsung SDI	KTMC1050GFA



## 信頼性データの要約:

デバイス名: RHRG75120RMS : U56686パッケージ: TO247

テスト	仕様	条件	間隔	結果
HTRB	JESD22-A108	Ta = 175°C for device, bias = 80% of max rated	1008 hrs	0/77
HTSL	JESD22-A103	Ta = 175°C for 1008 hours	1008 hrs	0/77
TC	JESD22-A104	Temp = -55°C to +150°C; for 1000 cycles	1000 cyc	0/77
H3TRB	JESD22-A101	Temp = 85C, RH=85%, bias = 80% of rated V or 100V max	1008 hrs	0/77
RSH	JESD22-B106	265 °C Immersion and 10s	10s	0/10
SD	J STD 002	Ta=245°C 5 sec dwell	5s	0/15
PD		Per Case Outline		0/10
Tri-temp		Tri-Temp Characterization, Per 48A		0/30
TR		Thermal Resistance		0/10

デバイス名: FGY75T120SQDNRMS : U56694パッケージ: TO247

テスト	仕様	条件	間隔	結果
HTRB	JESD22-A108	Ta = 175°C for device, bias = 80% of max rated	1008 hrs	0/77
HTGB	JESD22-A108	Ta = 175°C for 1008 hours, 100% rated Vgs	1008 hrs	0/77
HTSL	JESD22-A103	Ta = 175°C for 1008 hours	1008 hrs	0/77
TC	JESD22-A104	Temp = -55°C to +150°C; for 1000 cycles	1000 cyc	0/77
HAST	JESD22 A110	Temp= +110°C, RH=85% , 264hr, bias = 80% of rated V or 100V max	264hrs	0/77
RSH	JESD22-B106	265 °C Immersion and 10s	10s	0/10
SD	J STD 002	Ta=245°C 5 sec dwell	5s	0/15
PD		Per Case Outline		0/10
Tri-temp		Tri-Temp Characterization, Per 48A		0/30
TR		Thermal Resistance		0/10

デバイス名: FGY160T65SPD-F085RMS : U56679パッケージ: TQ247

テスト	仕様	条件	間隔	結果
HTRB	JESD22-A108	Ta = 175°C for device, bias = 100% of max rated	1008 hrs	0/231
HTGB	JESD22-A108	Ta = 175°C for 1008 hours, 100% rated Vgs	1008 hrs	0/231
HTSL	JESD22-A103	Ta = 175°C for 1008 hours	1008 hrs	0/231
TC	JESD22-A104	Temp = -55°C to +150°C; for 1000 cycles	1000 cyc	0/231
IOL	MIL STD750, M 1037	Ta=+25°C, delta Tj=100°C max, Ton=Toff is 3.5min	8572Cyc	0/231
	AEC Q101			
H3TRB	JESD22-A101	Temp = 85°C, RH=85%, bias = 80% of rated V or 100V max	1008hrs	0/231
RSH	JESD22-B106	265 °C Immersion and 10s	10s	0/30
SD	J STD 002	Ta=245°C 5 sec dwell	5s	0/45
PD		Per Case Outline		0/30
Tri-temp		Tri-Temp Characterization, Per 48A		0/90
TR		Thermal Resistance		0/30
CDPA TCDT	AEC Q101, rev D, test 7A (alt)	Custom Destructive Physical Analysis - TC Delamination Test, Post 1000 cyc TC		0/66
CDPA SAT	AEC-006	Post HTRB, HTGB		0/66
DPA	AEC-Q101-004 Section 4	Destructive Physical Analysis		0/6
		Post TC, H3TRB, HTRB, HTGB		
CDPA WP BS	MIL 883E, AEC -006	Custom Destructive Physical Analysis - Wire Pull, Ball Shear		0/18
		Post TC, HTRB, HTGB		
CDPA X Section	AEC -006	Post TC, HTRB, HTGB		0/9
Shift		Shift Analysis for HTRB/HTGB/HTSL/TC/IOL/H3TRB		Pass

デバイス名: FGY75T120SQDNRMS : U56694パッケージ: TQ247

テスト	仕様	条件	間隔	結果
HTRB	JESD22-A108	Ta = 175°C for device, bias = 80% of max rated	1008 hrs	0/77
HTGB	JESD22-A108	Ta = 175°C for 1008 hours, 100% rated Vgs	1008 hrs	0/77
HTSL	JESD22-A103	Ta = 175°C for 1008 hours	1008 hrs	0/77
TC	JESD22-A104	Temp = -55°C to +150°C; for 1000 cycles	1000 cyc	0/77
HAST	JESD22 A110	Temp= +110°C, RH=85% , 264hr, bias = 80% of rated V or 100V max	264hrs	0/77
RSH	JESD22-B106	265 °C Immersion and 10s	10s	0/10
SD	J STD 002	Ta=245°C 5 sec dwell	5s	0/15
PD		Per Case Outline		0/10
Tri-temp		Tri-Temp Characterization, Per 48A		0/30
TR		Thermal Resistance		0/10



デバイス名: FGY160T65SPD-F085

RMS : U56679

パッケージ : TO247

テスト	仕様	条件	間隔	結果
HTRB	JESD22-A108	Ta = 175°C for device, bias = 100% of max rated	1008 hrs	0/231
HTGB	JESD22-A108	Ta = 175°C for 1008 hours, 100% rated Vgs	1008 hrs	0/231
HTSL	JESD22-A103	Ta = 175°C for 1008 hours	1008 hrs	0/231
TC	JESD22-A104	Temp = -55°C to +150°C; for 1000 cycles	1000 cyc	0/231
IOL	MIL STD750, M 1037	Ta=+25°C, delta Tj=100°C max, Ton=Toff is 3.5min	8572Cyc	0/231
	AEC Q101			
H3TRB	JESD22-A101	Temp = 85°C, RH=85%, bias = 80% of rated V or 100V max	1008hrs	0/231
RSH	JESD22-B106	265 °C Immersion and 10s	10s	0/30
SD	J STD 002	Ta=245°C 5 sec dwell	5s	0/45
PD		Per Case Outline		0/30
Tri-temp		Tri-Temp Characterization, Per 48A		0/90
TR		Thermal Resistance		0/30
CDPA TCDT	AEC Q101, rev D, test 7A (alt)	Custom Destructive Physical Analysis - TC Delamination Test, Post 1000 cyc TC		0/66
CDPA SAT	AEC-006	Post HTRB, HTGB		0/66
DPA	AEC-Q101-004 Section 4	Destructive Physical Analysis		0/6
		Post TC, H3TRB, HTRB, HTGB		
CDPA WP BS	MIL 883E, AEC -006	Custom Destructive Physical Analysis - Wire Pull, Ball Shear		0/18
		Post TC, HTRB, HTGB		
CDPA X Section	AEC -006	Post TC, HTRB, HTGB		0/9
Shift		Shift Analysis for HTRB/HTGB/HTSL/TC/IOL/H3TRB		Pass

デバイス名: FFSH40120ADN-F085

RMS : U56690

パッケージ : TO247

テスト	仕様	条件	間隔	結果
HTRB	JESD22-A108	Ta = 175°C for device, bias = 100% of max rated	1008 hrs	0/231
HTSL	JESD22-A103	Ta = 175°C for 1008 hours	1008 hrs	0/231
TC	JESD22-A104	Temp = -55°C to +150°C; for 1000 cycles	1000 cyc	0/231
HAST	JESD22 A110	Temp= +110°C, RH=85% , 264hr, bias = 80% of rated V or 100V max	264hrs	0/231
RSH	JESD22-B106	265 °C Immersion and 10s	10s	0/30
SD	J STD 002	Ta=245°C 5 sec dwell	5s	0/45
PD		Per Case Outline		0/30
Tri-temp		Tri-Temp Characterization, Per 48A		0/90
TR		Thermal Resistance		0/30
CDPA TCDT	AEC Q101, rev D, test 7A (alt)	Custom Destructive Physical Analysis - TC Delamination Test, Post 1000 cyc TC		0/66
CDPA SAT	AEC-006	Post HTRB		0/66
DPA	AEC-Q101-004 Section 4	Destructive Physical Analysis		0/6
		Post TC, HAST, HTRB		
CDPA WP BS	MIL 883E, AEC -006	Custom Destructive Physical Analysis - Wire Pull, Ball Shear		0/18
		Post TC, HTRB		
CDPA X Section	AEC -006	Post TC, HTRB		0/9
Shift		Shift Analysis for HTRB/HTGB/HTSL/TC/IOL/HAST		Pass

すべての信頼性結果が合格。



電気的特性の要約: 電気的特性への影響はありません。

#### 影響を受ける部品の一覧:

注: 部品一覧には標準部品番号 (既製品) のみが記載されています。本 PCN の影響を受けるカスタム部品番号は、PCN メールで提供される顧客個別の付録、または PCN カスタマイズポータルに記載されています。

部品番号	認定試験用ピークル
FFH30S60STU	RHRG75120
FFH60UP40S3	RHRG75120
FFH60UP60S	RHRG75120
FFH60UP60S3	RHRG75120
ISL9K3060G3	RHRG75120
ISL9R1560G2	RHRG75120
ISL9R3060G2	RHRG75120
RHRG30120	RHRG75120
RHRG5060	RHRG75120
RHRG75120	RHRG75120
RURG3060	RHRG75120
RURG5060	RHRG75120
RURG8060	RHRG75120
FGH30S130P	FGY160T65SPD-F085
FGH30S150P	FGY160T65SPD-F085
FGH40N60UFTU	FGY160T65SPD-F085
FGH40T120SMDL4	FGY160T65SPD-F085
FGH50N6S2D	FGY160T65SPD-F085
FGH50T65SQD-F155	FGY160T65SPD-F085
FGH60N60SFDTU	FGY160T65SPD-F085
FGH60N60SFTU	FGY160T65SPD-F085
FGH60N60SMD	FGY160T65SPD-F085
FGH60N60UFDTU	FGY160T65SPD-F085
FGH60T65SQD-F155	FGY160T65SPD-F085
FGH75N60UFTU	FGY160T65SPD-F085
FGH75T65SQD-F155	FGY160T65SPD-F085
FGH75T65SQDNL4	FGY160T65SPD-F085
FGH75T65SQDT-F155	FGY160T65SPD-F085
FGH75T65SQDTL4	FGY160T65SPD-F085
FGH75T65UPD-F155	FGY160T65SPD-F085



FGH80N60FDTU	FGY160T65SPD-F085
FGY40T120SMD	FGY160T65SPD-F085
FGY75N60SMD	FGY160T65SPD-F085
HGTG30N60B3D	FGY160T65SPD-F085
HGTG7N60A4D	FGY160T65SPD-F085
FGHL50T65SQ	FGY160T65SPD-F085
FGHL40S65UQ	FGY160T65SPD-F085
FGY75T120SQDN	FGY75T120SQDN
FGH40T120SQDNL4	FGY75T120SQDN
FGY60T120SQDN	FGY75T120SQDN
FFSH10120A	FFSH40120ADN-F085
FFSH10120ADN-F155	FFSH40120ADN-F085
FFSH15120A	FFSH40120ADN-F085
FFSH15120ADN-F155	FFSH40120ADN-F085
FFSH1665A	FFSH40120ADN-F085
FFSH1665ADN-F155	FFSH40120ADN-F085
FFSH20120A	FFSH40120ADN-F085
FFSH20120ADN-F155	FFSH40120ADN-F085
FFSH2065A	FFSH40120ADN-F085
FFSH2065ADN-F155	FFSH40120ADN-F085
FFSH30120A	FFSH40120ADN-F085
FFSH30120ADN-F155	FFSH40120ADN-F085
FFSH3065A	FFSH40120ADN-F085
FFSH3065ADN-F155	FFSH40120ADN-F085
FFSH40120A	FFSH40120ADN-F085
FFSH40120ADN-F155	FFSH40120ADN-F085
FFSH4065A	FFSH40120ADN-F085
FFSH4065ADN-F155	FFSH40120ADN-F085
FFSH50120A	FFSH40120ADN-F085
FFSH5065A	FFSH40120ADN-F085
FFSH5065A-F155	FFSH40120ADN-F085
NTHL080N120SC1	SVHL080N120SC1
NTH4L080N120SC1	SVHL080N120SC1
FCH041N65EF-F155	FCH041N60F-F085
FCH041N65EFL4	FCH041N60F-F085
FCH041N65F-F155	FCH041N60F-F085



FCH043N60	FCH041N60F-F085
FCH060N80-F155	FCH041N60F-F085
FCH070N60E	FCH041N60F-F085
FCH072N60F	FCH041N60F-F085
FCH077N65F-F155	FCH041N60F-F085
FCH085N80-F155	FCH041N60F-F085
FCH099N60E	FCH041N60F-F085
FCH104N60	FCH041N60F-F085
FCH104N60F	FCH041N60F-F085
FCH110N65F-F155	FCH041N60F-F085
FCH125N60E	FCH041N60F-F085
FCH150N65F-F155	FCH041N60F-F085
FCH165N60E	FCH041N60F-F085
FCH190N65F-F155	FCH041N60F-F085
FDH038AN08A1	FCH041N60F-F085
FDH055N15A	FCH041N60F-F085
FDH210N08	FCH041N60F-F085
FDH44N50	FCH041N60F-F085
FQH8N100C	FCH041N60F-F085
HUF75345G3	FCH041N60F-F085
HUF75652G3	FCH041N60F-F085
HUF75852G3	FCH041N60F-F085
FCH041N65EFLN4	FCH041N60F-F085